

7700W, 24V Surface Mount Transient Voltage Suppressor



FEATURES

- AEC-Q101 qualified
- Bidirectional type
- Low clamping voltage
- Low leakage current
- T_J =175 °C capability suitable for high reliability and automotive requirement
- Meets ISO 7637-2 and ISO 16750-2 surge specifications (Varied by test conditions)
- IEC-61000-4-2 ESD 30kV(Air), 30kV(Contact)
- Moisture sensitivity level: level 1, per J-STD-020
- RoHS Compliant
- Halogen-free

APPLICATIONS

• Transient Surge Protection

MECHANICAL DATA

- Case: DO-218AB
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 2 whisker test
- Weight: 2.66g (approximately)

KEY PARAMETERS						
PARAMETER	VALUE	UNIT				
Vwм	24	V				
V _{BR}	29.5	V				
Рррм	7700	W				
T _{J MAX}	175	°C				
Package	DO-218AB					





DO-218AB



ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER	SYMBOL	VALUE	UNIT		
Non-repetitive peak impulse power dissipation with 10/1000µs waveform ⁽¹⁾	Рерм	7700	W		
Junction temperature	TJ	-55 to +175	°C		
Storage temperature	Tstg	-55 to +175	°C		

Notes:

1. Non-repetitive current pulse per Fig.3



LTD7S24CAH

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ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)										
Part number	Device marking	volt V _{BR} (\	a down age at I⊤ /) re 1)	Test current I⊤ (mA)	Working stand-off voltage V _{WM} (V)	current I _R at V _{WM} (μΑ)	Maximum blocking leakage current I _R at V _{WM} T _J =175°C (μA)	Maximum peak impulse current IPPM (A) tp =10/1000	Typical clamping voltage V _C at I _{PPM} (V)	Typical temp. coefficient of V _{BR} αT (%/°C) (Note 2)
		Min	Max			(Note 1)	(Note 1)	μs)		
LTD7S24CAH	LTD7S24	26.7	29.5	5	24	1	150	300	24	0.081

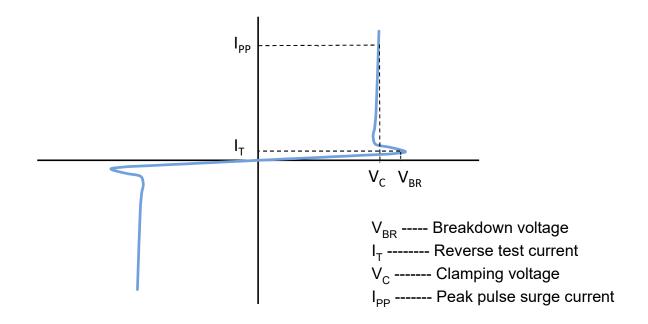
Notes:

1. Pulse test with PW = 30ms

2. To calculate V_{BR} vs. junction temperature, use the following formula: V_{BR} at T_J = V_{BR} at 25 °C x (1 + α T x (T_J - 25))

ORDERING INFORMATION					
ORDERING CODE	PACKAGE	PACKING			
LTD7S24CAH	DO-218AB	750 / Tape & Reel			

I - V CURVE CHARACTERISTICS





CHARACTERISTICS CURVES

(T_A = 25°C unless otherwise noted)

120 PERCENT OF POWER PULSE POWER (%) 100 80 60 40 20 0 25 50 150 175 200 0 75 100 125 AMBIENT TEMPERATURE (°C) Fig.3 10/1000µs pulse waveform

PEAK PULSE POWER (KW)

Fig.1 Peak Pulse Power Derating Curve

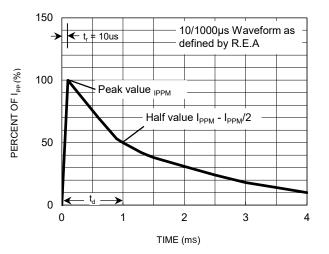


Fig.5 Typical Junction Capacitance

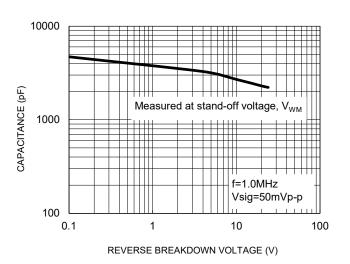


Fig.2 Non-Repetitive Peak Pulse Power vs. Pulse Time

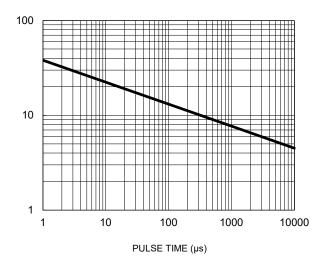
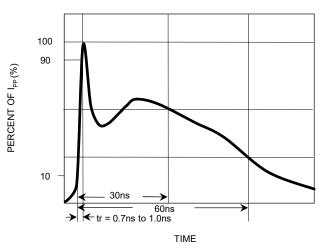
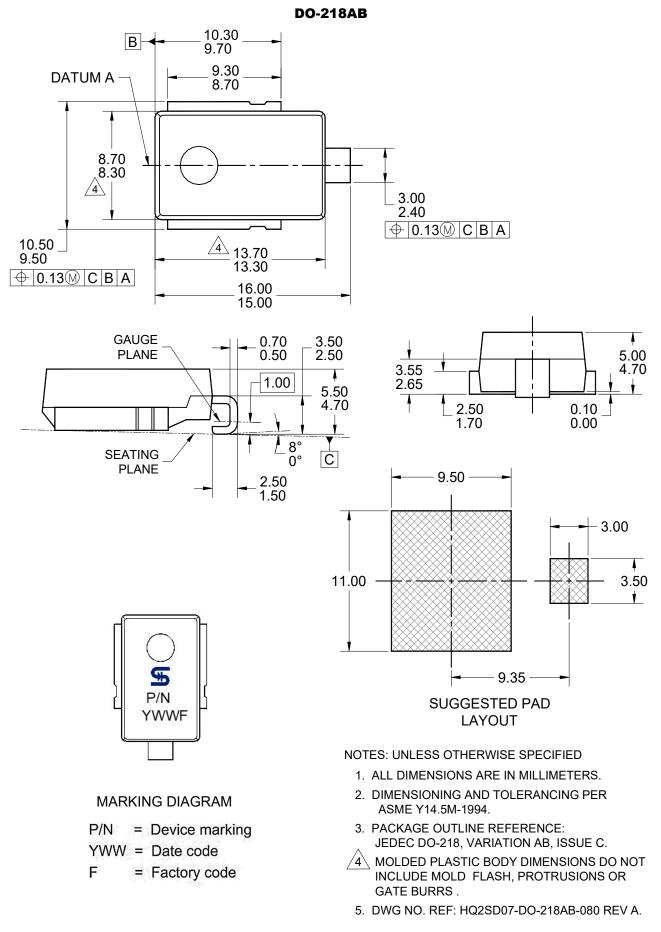


Fig.4 ESD pulse waveform





PACKAGE OUTLINE DIMENSIONS





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